3.6MHz, Rail-to-Rail I/O CMOS Operational Amplifier

1 FEATURES

- **HIGH GAIN BANDWIDTH:3.6MHz**
- **RAIL-TO-RAIL INPUT AND OUTPUT ±0.8mV Typical Vos**
- **INPUT VOLTAGE RANGE: -0.1V to +5.6V with Vs = 5.5V**
- **SUPPLY RANGE: +2.5V to +5.5V**
- **SPECIFIED UP TO +125°C**
- **Micro SIZE PACKAGES: SOIC-8**

2 APPLICATIONS

- **SENSORS**
- **PHOTODIODE AMPLIFICATION**
- **ACTIVE FILTERS**
- **TEST EQUIPMENT**
- **DRIVING A/D CONVERTERS**

3 DESCRIPTIONS

The RES2314IDR families of products offer low voltage operation and rail-to-rail input and output, as well as excellent speed/power consumption ratio, providing an excellent bandwidth (3.6MHz) and slew rate of 1.8V/us. The op-amps are unity gain stable and feature an ultra-low input bias current.

The RES2314IDR families of operational amplifiers are specified at the full temperature range of -40°C to +125°C under single or dual power supplies of 2.5V to 5.5V.

Device Information (1)

PART NUMBER	PACKAGE	BODY SIZE(NOM)
RES2314IDR	SOIC8	4.90mm×3.90mm

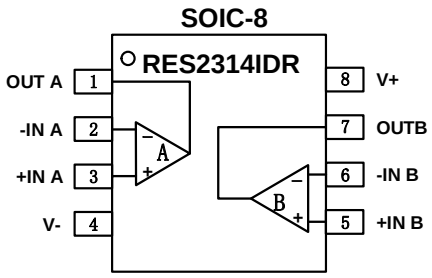
(1) For all available packages, see the orderable addendum at the end of the data sheet.

5 PACKAGE/ORDERING INFORMATION (1)

Orderable Device	Package Type	Pin	Channel	Op Temp(°C)	Device Marking (2)	Package Qty
RES2314IDR	SOIC8	8	2	-40°C ~125°C	RES2314IDR	Tape and Reel,4000

NOTE:
(1) This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the right-hand navigation.
(2) There may be additional marking, which relates to the lot trace code information (data code and vendor code), the logo or the environmental category on the device.

Pin Configuration and Functions (Top View)



Pin Description

NAME	RES2314IDR		I/O (1)	DESCRIPTION
	SOIC-8			
-INA	2		I	Inverting input, channel A
+INA	3		I	Noninverting input, channel A
-INB	6		I	Inverting input, channel B
+INB	5		I	Noninverting input, channel B
OUTA	1		O	Output, channel A
OUTB	7		O	Output, channel B
EnA	-		I	Enable pin, channel A. This pin turns the regulator on or off. Low = disabled, high = normal operation (pin must be driven)
EnB	-		I	Enable pin, channel B. This pin turns the regulator on or off. Low = disabled, high = normal operation (pin must be driven)
V-	4		-	Negative (lowest) power supply
V+	8		-	Positive (highest) power supply

(1) I = Input, O = Output.

7 SPECIFICATIONS

7.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
Voltage	Supply, Vs=(V+) - (V-)			7	V
	Signal input pin (2)		(V-)-0.5	(V+) +0.5	
	Signal output pin (3)		(V-)-0.5	(V+) +0.5	
Current	Signal input pin (2)		-10	10	mA
	Signal output pin (3)		-100	100	mA
	Output short-circuit (4)		Continuous		
θ_{JA}	Package thermal impedance (5)				°C/W
		SOIC-8		110.88	
Temperature	Operating range, T_A		-40	125	°C
	Junction, T_J (6)		-40	150	
	Storage, T_{stg}		-65	150	

(1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
(2) Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails should be current-limited to 10mA or less.
(3) Output terminals are diode-clamped to the power-supply rails. Output signals that can swing more than 0.5V beyond the supply rails should be current-limited to ±100mA or less.
(4) Short-circuit to ground, one amplifier per package.
(5) The package thermal impedance is calculated in accordance with JESD-51.
(6) The maximum power dissipation is a function of $T_{J(MAX)}$, $R_{\theta JA}$, and T_A. The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} - T_A) / R_{\theta JA}$. All numbers apply for packages soldered directly onto a PCB.

7.2 ESD Ratings

The following ESD information is provided for handling of ESD-sensitive devices in an ESD protected area only.

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±5000	V
		Machine Model (MM)	±400	

(1) JEDEC document JEP155 states that 500 V HBM allows safe manufacturing with a standard ESD control process.

ESD SENSITIVITY CAUTION

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

7.3 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
Supply voltage，Vs= (V+) - (V-)	Single-supply	2.5		5.5	V
	Dual-supply	±1.25		±2.75	

7.4 ELECTRICAL CHARACTERISTICS

(At T_A = +25°C, Vs=5V, R_L = 10kΩ connected to V_S/2, and V_{OUT} = V_S/2, V_{CM}= V_S/2, Full [9] = -40°C to +125°C, unless otherwise noted.) [1]

PARAMETER		CONDITIONS	T_J	RES2314IDR			
				MIN[2]	TYP[3]	MAX[2]	UNIT
POWER SUPPLY							
V_S	Operating Voltage Range		25°C	2.5		5.5	V
IQ	Quiescent Current/Amplifier		25°C		260	350	uA
PSRR	Power-Supply Rejection Ratio	V_S=2.5V to 5.5V V_{CM}=(V-)+0.5V	25°C	76	86		dB
			Full	69			
INPUT							
V_{OS}	Input Offset Voltage	V_{CM}= V_S/2	25°C	-3	±0.8	3	mV
V_{OS} T_C	Input Offset Voltage Average Drift	V_{CM}= V_S/2	Full		±2		uV/°C
IB	Input Bias Current [4] [5]		25°C		±1	±10	pA
I_{OS}	Input Offset Current [4]		25°C		±1	±10	pA
V_{CM}	Common-Mode Voltage Range	V_S= 5.5V	25°C	-0.1		5.6	V
CMRR	Common-Mode Rejection Ratio	V_S= 5.5V V_{CM}=-0.1V to 4V	25°C	76	87		dB
			Full	71			
		V_S= 5.5V V_{CM}=-0.1V to 5.6V	25°C	62	71		
			Full	60			
OUTPUT							
A_{OL}	Open-Loop Voltage Gain	R_L=2KΩ Vo=0.15V to 4.85V	25°C	100	107		dB
			Full	86			
		R_L=10KΩ Vo= 0.05V to 4.95V	25°C	100	110		
			Full	87			
	Output Swing From Rail	R_L=2KΩ	25°C		31		mV
		R_L=10KΩ			7		
I_{OUT}	Output Short-Circuit Current [6] [7]		25°C		±80		mA
FREQUENCY RESPONSE							
SR	Slew Rate [8]		25°C		1.8		V/us
GBP	Gain-Bandwidth Product		25°C		3.6		MHz
PM	Phase Margin		25°C		65		°
t_S	Setting Time,0.1%				0.5		us
	Overload Recovery Time	V_{IN}·Gain≥V_S			0.7		us
NOISE							
e_n	Input Voltage Noise Density	f = 1KHz	25°C		15		nV/$\sqrt{\text{Hz}}$
		f = 10KHz	25°C		13		nV/$\sqrt{\text{Hz}}$
ENABLE/SHUTDOWN <RS2314IDR >							
$I_{Q(OFF)}$	Supply Current in Shutdown		25°C		<1		uA
t_{OFF}			25°C		3		us
t_{ON}			25°C		20		us
V_L	Shut Down		25°C	V-		(V-)+0.8	V
V_H	Amplifier Is Active		25°C	(V-)+2		V+	V

NOTE:

(1) Electrical table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device.

(2) Limits are 100% production tested at 25°C. Limits over the operating temperature range are ensured through correlations using statistical quality control (SQC) method.

7.5 TYPICAL CHARACTERISTICS

NOTE: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only.

At T_A = +25°C, Vs=5V, R_L = 10kΩ connected to $V_S/2$, V_{OUT} = $V_S/2$, unless otherwise noted.

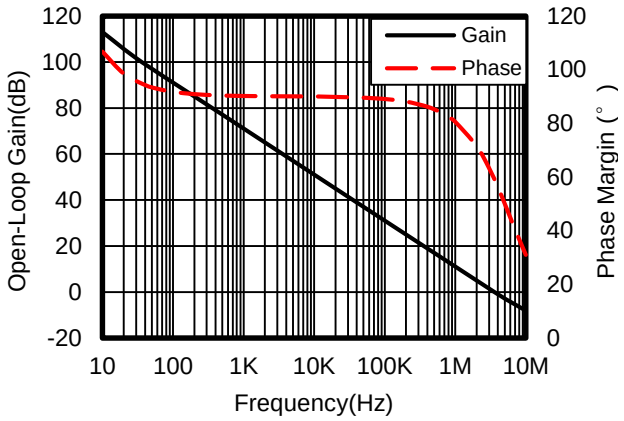


Figure 1. Open-Loop Gain and Phase vs Frequency

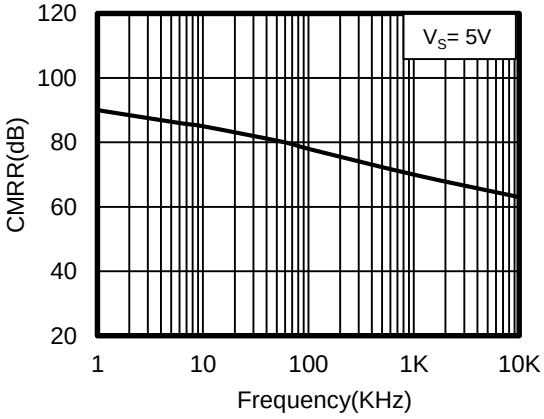


Figure 2. Common-Mode Rejection Ratio vs Frequency

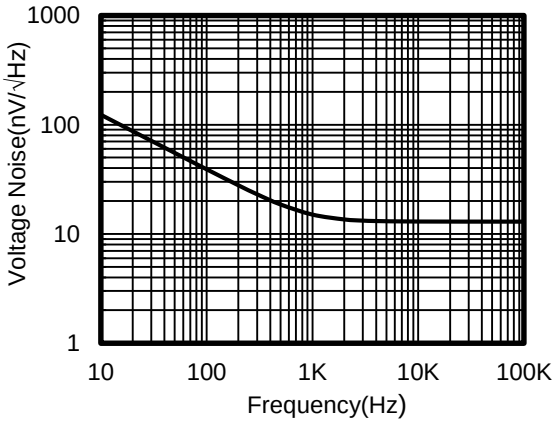


Figure 3. Input Voltage Noise Spectral Density vs Frequency

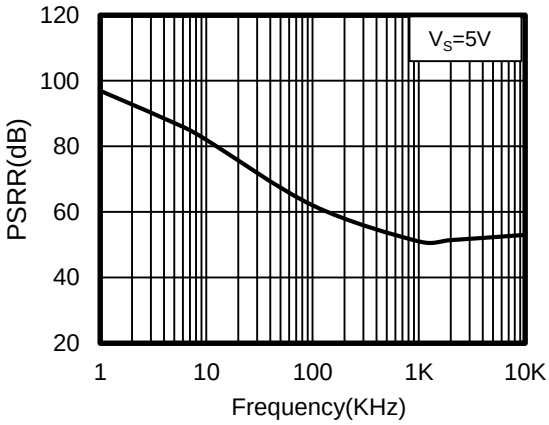


Figure 4. Power-Supply Rejection Ratio vs Frequency

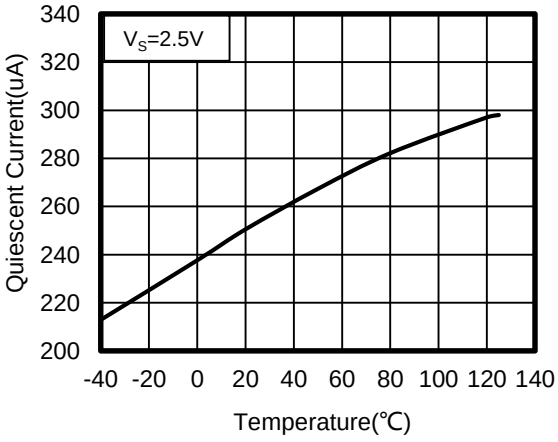


Figure 5. Quiescent Current vs Temperature

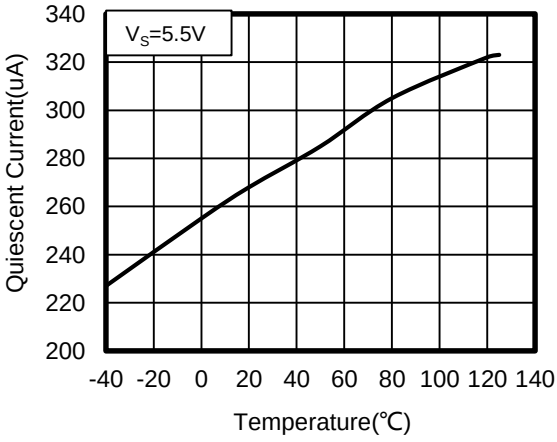


Figure 6. Quiescent Current vs Temperature

TYPICAL CHARACTERISTICS

NOTE: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only.

At T_A = +25°C, Vs=5V, R_L = 10kΩ connected to $V_S/2$, V_{OUT} = $V_S/2$, unless otherwise noted.

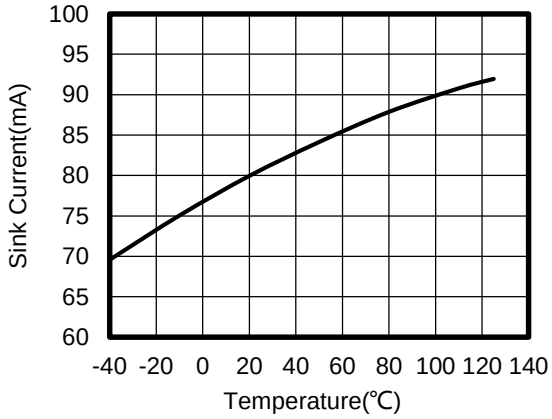


Figure 7. Sink Current vs Temperature

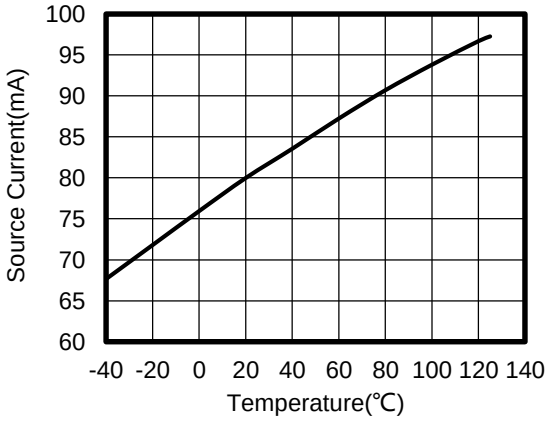


Figure 8. Source Current vs Temperature

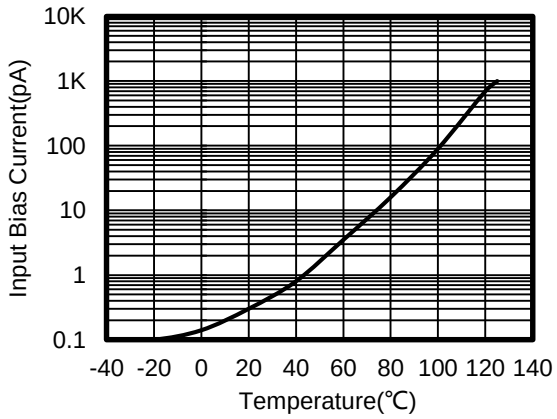


Figure 9. Input Bias Current vs Temperature

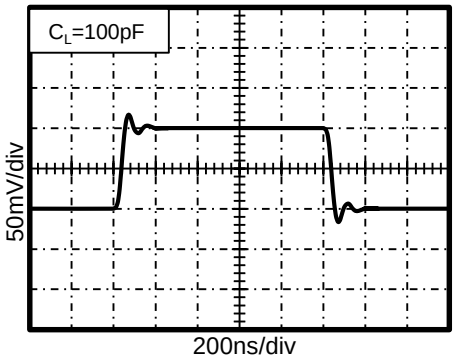


Figure 10. Small-Signal Step Response

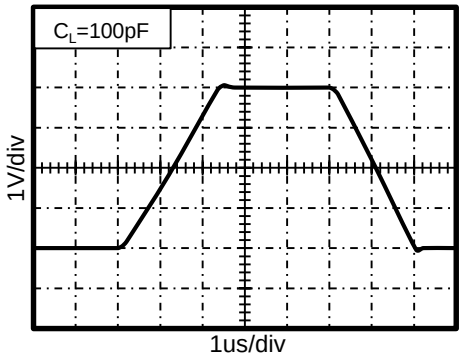


Figure 11. Large-Signal Step Response

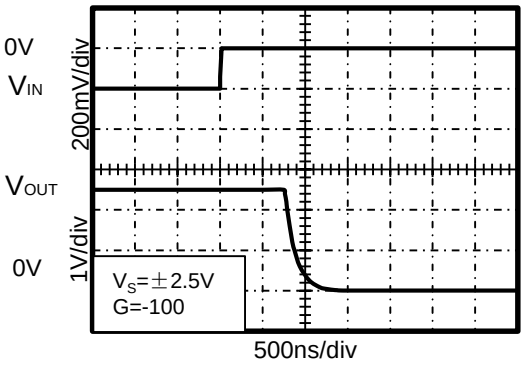


Figure 12. Positive Overvoltage Recovery

TYPICAL CHARACTERISTICS

NOTE: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only.

At T_A = +25°C, Vs=5V, R_L = 10kΩ connected to $V_S/2$, V_{OUT} = $V_S/2$, unless otherwise noted.

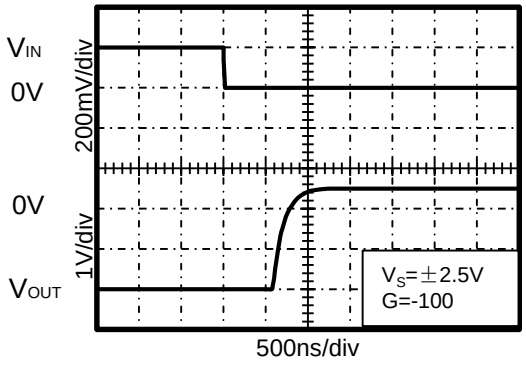


Figure 13. Negative Overvoltage Recovery

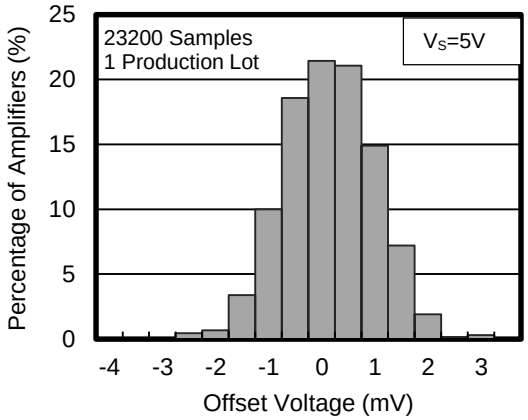


Figure 14. Offset Voltage Production Distribution

8 Detailed Description

8.1 Overview

The RES2314IDR are high precision, rail-to-rail operational amplifiers that can be run from a single-supply voltage 2.5V to 5.5V (±1.25V to ±2.75V). Supply voltages higher than 7V (absolute maximum) can permanently damage the amplifier. Rail-to-rail input and output swing significantly increases dynamic range, especially in low-supply applications. Good layout practice mandates use of a 0.1uF capacitor place closely across the supply pins.

8.2 RS2314IDR ENABLE FUNCTION

The RES2314IDR includes a shutdown mode. Under logic control, the amplifiers can be switched from normal mode to a standby current of 1uA. When the Enable pin is connected to high, the amplifier is active. Connecting Enable low disables the amplifier, and places the amplifier, and place the output in a high-impedance state.

8.3 Phase Reversal Protection

The RES2314IDR family has internal phase-reversal protection. Many op amps exhibit phase reversal when the input is driven beyond the linear common-mode range. This condition is most often encountered in noninverting circuits when the input is driven beyond the specified common-mode voltage range, causing the output to reverse into the opposite rail. The input of the RES2314IDR prevents phase reversal with excessive common-mode voltage. Instead, the appropriate rail limits the output voltage. This performance is shown in figure 15.

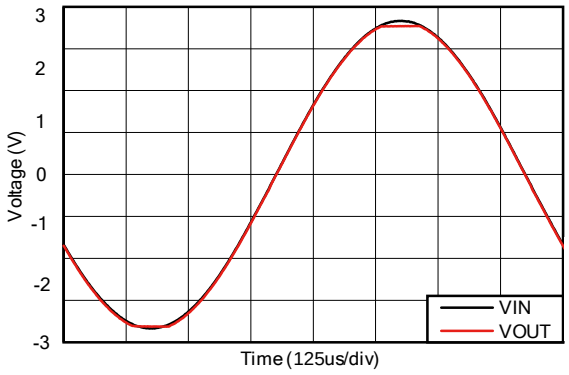


Figure 15. Output Waveform Devoid of Phase Reversal during a n Input Overdr i ve Condit i on

8.4 EMI Rejection Ratio (EMIRR)

The electromagnetic interference (EMI) rejection ratio, or EMIRR, describes the EMI immunity of operational amplifiers. An adverse effect that is common to many operational amplifiers is a change in the offset voltage as a result of RF signal rectification. An operational amplifier that is more efficient at rejecting this change in offset as a result of EMI has a higher EMIRR and is quantified by a decibel value. Measuring EMIRR can be performed in many ways, but this document provides the EMIRR IN+, which specifically describes the EMIRR performance when the RF signal is applied to the noninverting input pin of the operational amplifier. In general, only the noninverting input is tested for EMIRR for the following three reasons:

• Operational amplifier input pins are known to be the most sensitive to EMI, and typically rectify RF signals better than the supply or output pins.

• The noninverting and inverting operational amplifier inputs have symmetrical physical layouts and exhibit nearly matching EMIRR performance.

• EMIRR is easier to measure on noninverting pins than on other pins because the noninverting input pin can be isolated on a printed-circuit-board (PCB). This isolation allows the RF signal to be applied directly to the noninverting input pin with no complex interactions from other components or connecting PCB traces.

Detailed Description (continued)

The EMIRR IN+ of the RES2314is plotted versus frequency in Figure 16. If available, any dual and quad operational amplifier device versions have approximately identical EMIRR IN+ performance. The RES2314IDR unity-gain bandwidth is 3.7MHz. EMIRR performance below this frequency denotes interfering signals that fall within the operational amplifier bandwidth.

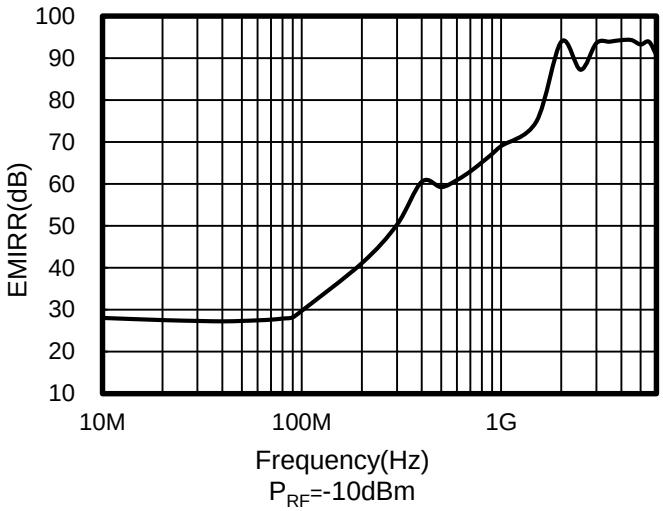


Figure 16. RES2314 EMIRR vs Frequency

8.5 EMIRR IN+ Test Configuration

Figure 17 shows the circuit configuration for testing the EMIRR IN+. An RF source is connected to the operational amplifier noninverting input pin using a transmission line. The operational amplifier is configured in a unity-gain buffer topology with the output connected to a low-pass filter (LPF) and a digital multimeter (DMM). A large impedance mismatch at the operational amplifier input causes a voltage reflection; however, this effect is characterized and accounted for when determining the EMIRR IN+. The resulting dc offset voltage is sampled and measured by the multimeter. The LPF isolates the multimeter from residual RF signals that can interfere with multimeter accuracy.

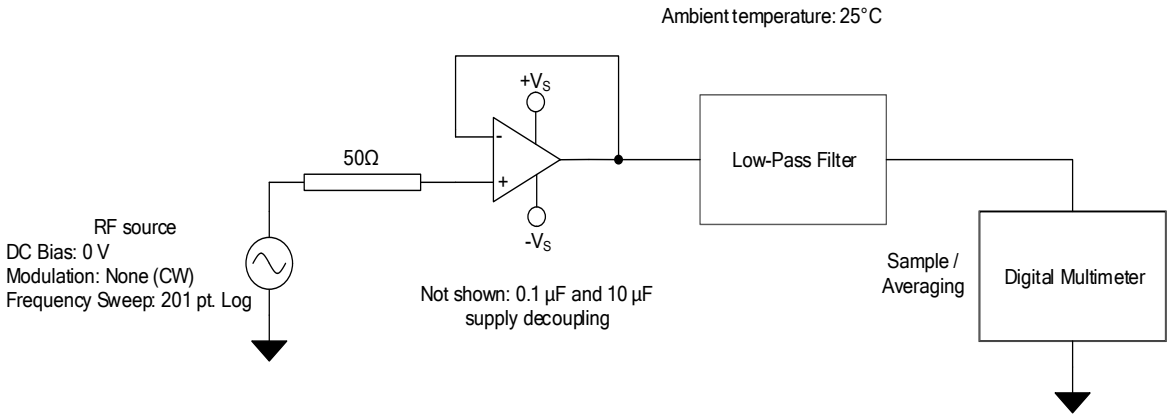


Figure 17. EMIRR IN+ Test Configuration Schematic

9 Application and Implementation

9.1 APPLICATION NOTE

TheRES2314are high precision, rail-to-rail operational amplifiers that can be run from a single-supply voltage 2.5V to 5.5V (±1.25V to ±2.75V). Supply voltages higher than 7V (absolute maximum) can permanently damage the amplifier. Rail-to-rail input and output swing significantly increases dynamic range, especially in low-supply applications. Good layout practice mandates use of a 0.1uF capacitor place closely across the supply pins.

Typical Applications

9.2 25-kHz Low-pass Filter

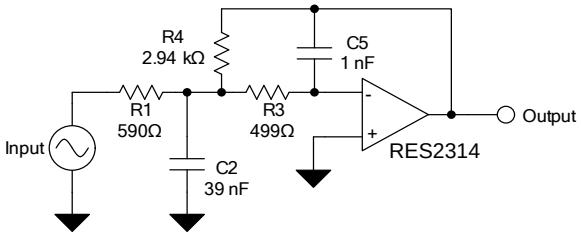


Figure 18. 25-kHz Low-Pass Filter

9.3 Design Requirements

Low-pass filters are commonly employed in signal processing applications to reduce noise and prevent aliasing. The RES2314devices are ideally suited to construct high-speed, high-precision active filters. Figure 18 shows a second-order, low-pass filter commonly encountered in signal processing applications.

Use the following parameters for this design example:

- Gain = 5 V/V (inverting gain)
- Low-pass cutoff frequency = 25 kHz
- Second-order Chebyshev filter response with 3-dB gain peaking in the passband

9.4 Detailed Design Procedure

The infinite-gain multiple-feedback circuit for a low-pass network function is shown in Figure 18. Use Equation 1 to calculate the voltage transfer function.

$$\frac{\text{Output}}{\text{Input}}(s) = \frac{-1/R_1 R_3 C_2 C_5}{s^2 + (s/C_2)(1/R_1 + 1/R_3 + 1/R_4) + 1/R_3 R_4 C_2 C_5} \quad (1)$$

This circuit produces a signal inversion. For this circuit, the gain at dc and the low-pass cutoff frequency are calculated by Equation 2:

$$\text{Gain} = \frac{R_4}{R_1}$$

$$f_C = \frac{1}{2\pi}\sqrt{(1/R_3 R_4 C_2 C_5)}$$

9.5 Application Curve

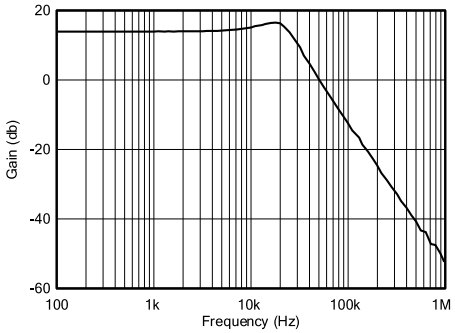


Figure 19. Low-pass filter transfer function

10 LAYOUT

10.1 Layout Guidelines

Attention to good layout practices is always recommended. Keep traces short. When possible, use a PCB ground plane with surface-mount components placed as close to the device pins as possible. Place a 0.1uF capacitor closely across the supply pins. These guidelines should be applied throughout the analog circuit to improve performance and provide benefits such as reducing the EMI susceptibility.

10.2 Layout Example

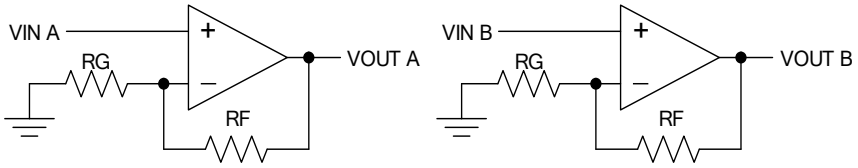


Figure 20. Schematic Representation

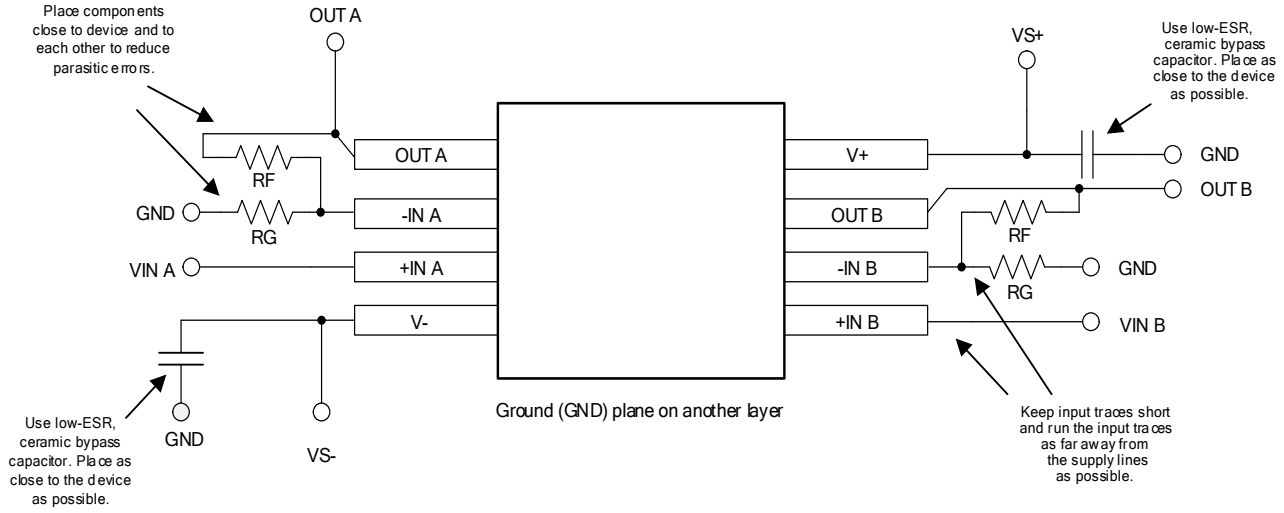
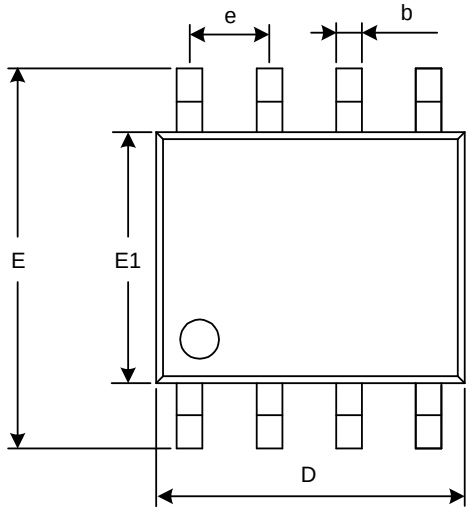
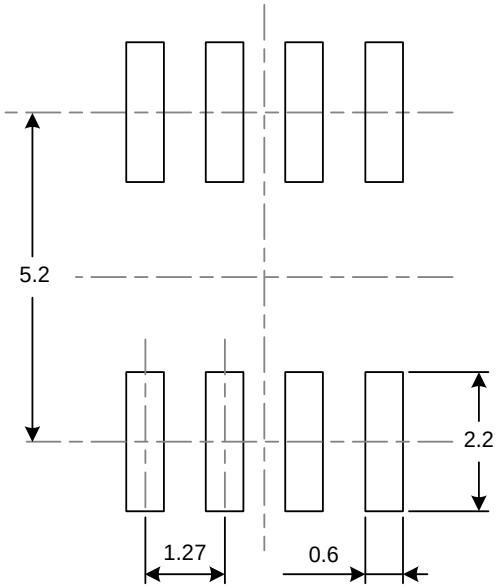


Figure 21. Layout Example

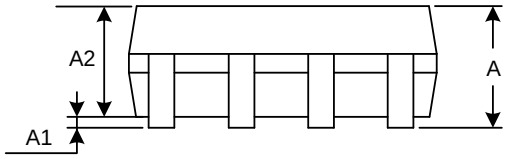
NOTE: Layout Recommendations have been shown for dual op-amp only, follow similar precautions for Single and four.

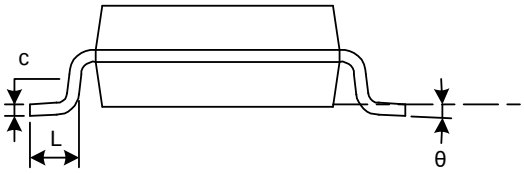
SOIC8





RECOMMENDED LAND PATTERN (Unit: mm)



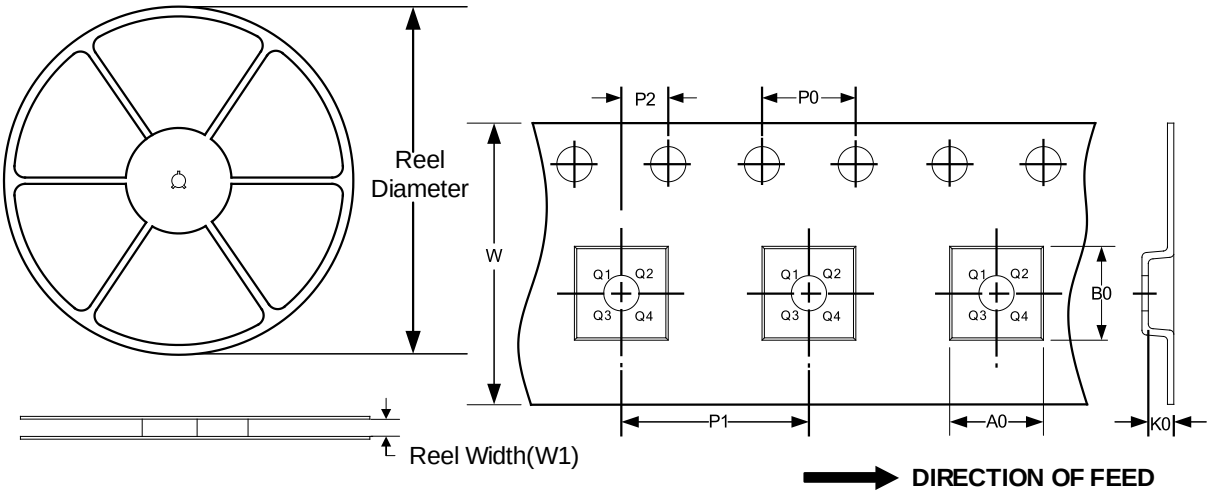


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270(BSC)		0.050(BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

12 TAPE AND REEL INFORMATION

REEL DIMENSIONS

TAPE DIMENSION



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel Diameter	Reel Width(mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
SOIC8	13"	12.4	6.40	5.40	2.10	4.0	8.0	2.0	12.0	Q1

NOTE:
1. All dimensions are nominal.
2. Plastic or metal protrusions of 0.15mm maximum per side are not included.